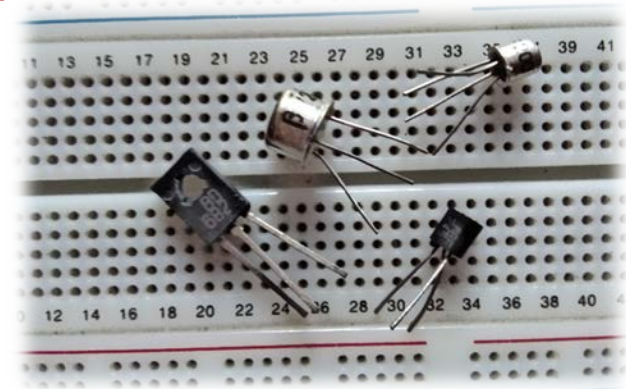




ELECTRONIC DEVICES

Assist. prof. Laura-Nicoleta IVANCIU, Ph.D.

C11 – Transistors. BJTs.



Contents

- Types of transistors
- Operating principle. Operating regions.
- n-type transistors. Transfer characteristics.
- p-type transistors. Transfer characteristics.
- Bipolar junction transistors (BJTs)

Transistors



- 1926 - JE Lilienfeld (physicist, engineer)
first patent of a field effect transistor – could not be built
- 1947, Bell Labs, USA - J Bardeenn, W Brattain, W Shockley
first built transistor
- 1956 J Bardeenn, W Brattain, W Shockley
Nobel prize in physics

The invention of the transistor in 1947 is included on the [list of IEEE milestones](#)

But what is a transistor?

Transistors

= **active** semiconductor devices, with three terminals

- used to amplify or switch signals
- essential components of electronic circuits
- discrete or integrated

Operating principle:

The **voltage** applied between two terminals (command) controls the **current** through the third terminal

transistors \equiv **voltage-controlled current sources**

Transistors

= **active** semiconductor devices, with three terminals

- used to amplify or switch signals
- essential components of electronic circuits
- discrete or integrated

“Putting sixty-four transistors on a chip allowed people to dream of the future.
Putting four million transistors on a chip actually gave them the future.”

- Malcolm Gladwell

Intel 4004, 1971, 10 μ , 14 mm², 2,300 transistors

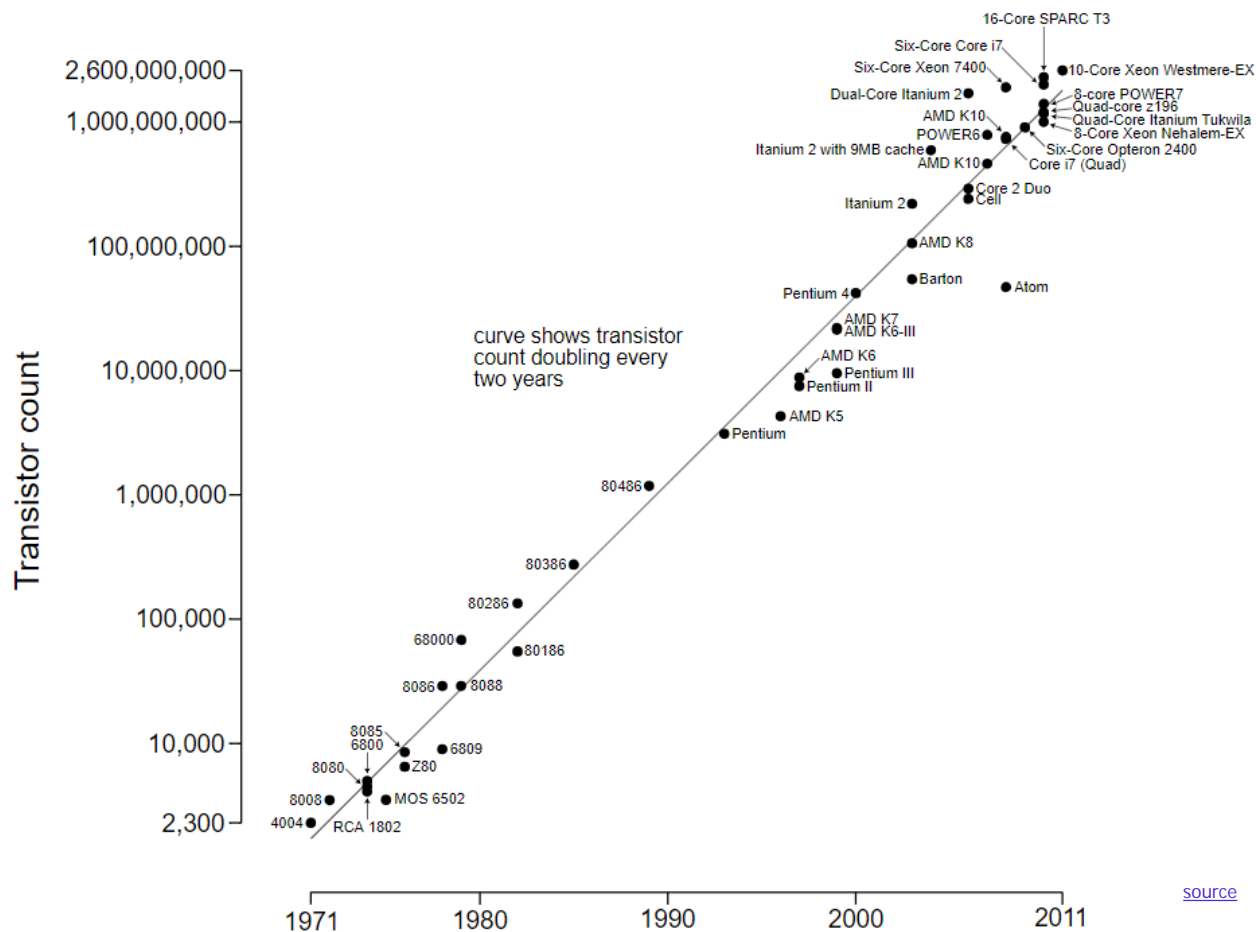
Pentium 4, 2006, 65 nm, 90 mm², 184,000,000 transistors

Core i7 Haswell-E, 8-core, 2014, 22 nm, 355 mm², 2,600,000,000 transistors

Xeon_Broadwell-E5, 22-core, 2016, 14 nm, 456 mm², 7,200,000,000 transistors

Transistors

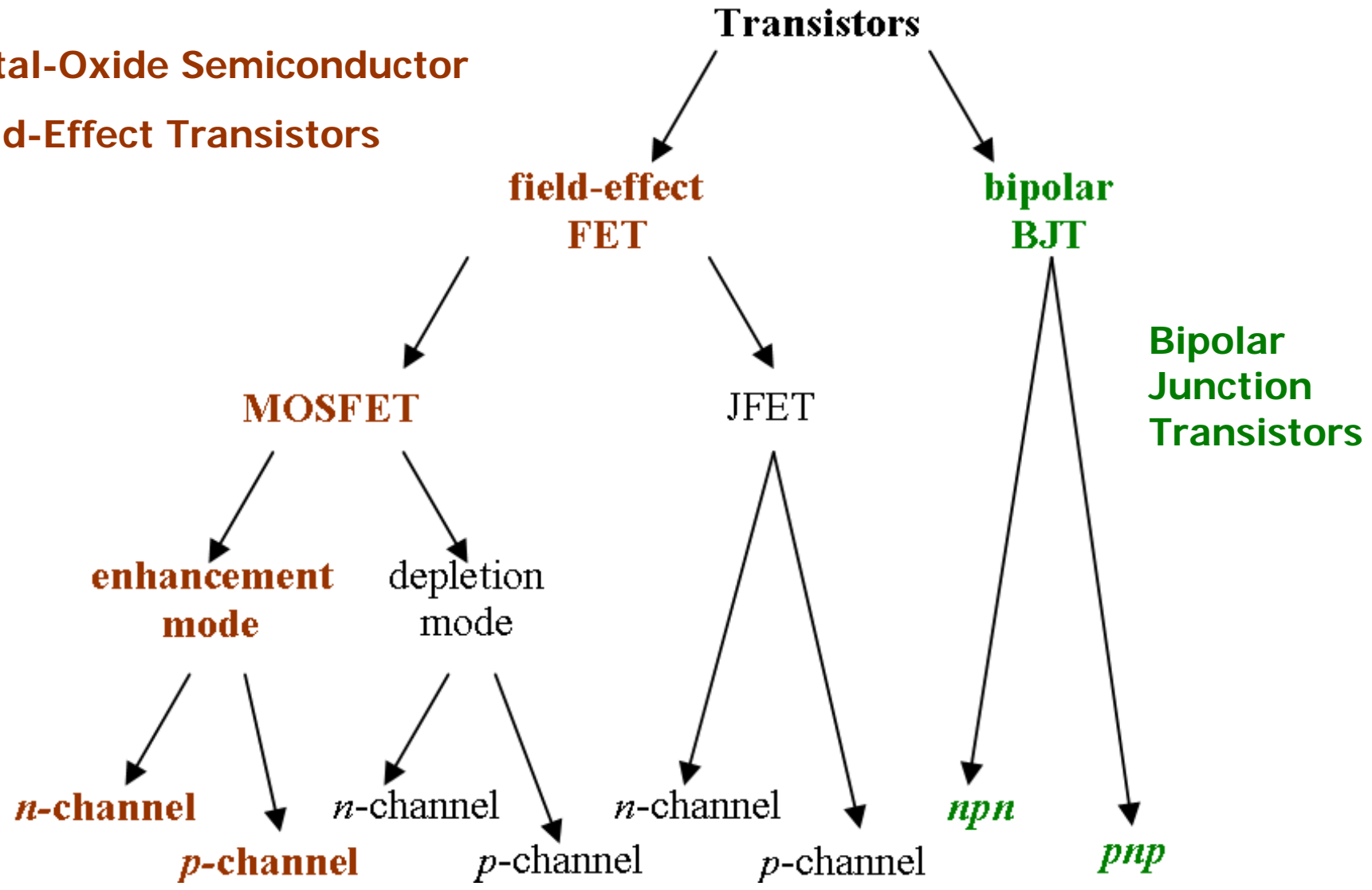
Microprocessor Transistor Counts 1971-2011 & Moore's Law



Moore's Law:

“The number of transistors and resistors on a chip doubles every 2 years”

Metal-Oxide Semiconductor
Field-Effect Transistors



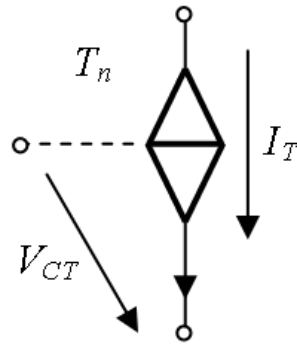
➤ Operating principle

transistors \equiv non linear **voltage-controlled current sources**

square – MOSFET; exponential – BJT

n-type

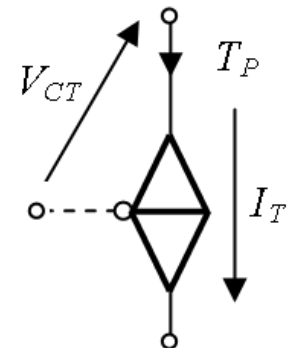
- n-channel MOSFET
- npn BJT



dc model – ideal VCCS

p-type

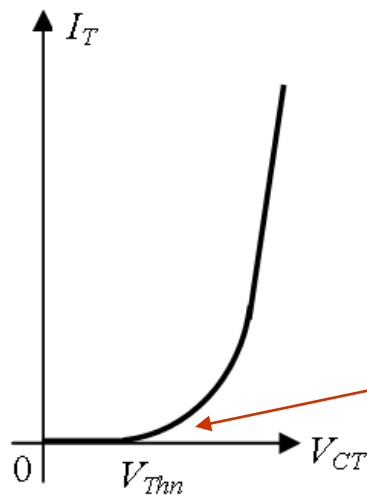
- p-channel MOSFET
- pnp BJT



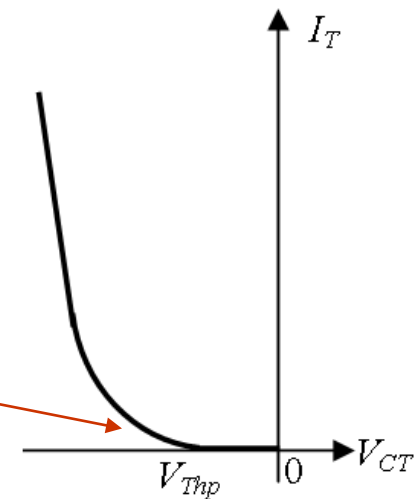
➤ Operating regions

transistors \equiv non linear **voltage-controlled current sources**

n-type



p-type



Threshold voltage

- $V_{CT} < V_{Thn}, T_n - \text{off}, I_T = 0$
- $V_{CT} > V_{Thn}, T_n - \text{on}, I_T > 0$

- $V_{CT} > V_{Thp}, T_p - \text{off}, I_T = 0$
- $V_{CT} < V_{Thp}, T_p - \text{on}, I_T > 0$

➤ n-type transistors

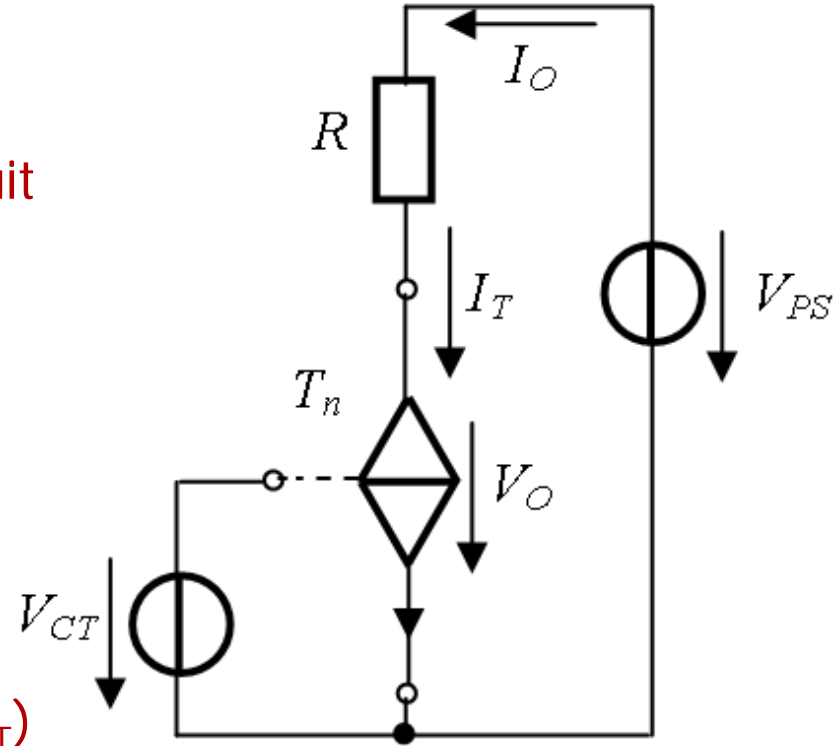
Using the n-type transistor, T_n , in a circuit

- series supply – voltage source
- parallel supply – current source

Output quantities: I_O , V_O

Transfer characteristics: $I_O(V_{CT})$, $V_O(V_{CT})$

$$I_T = I_O$$



Why is R necessary?

➤ Transfer characteristics

- $V_{CT} < V_{Thn}$, T_n – off, $I_O = I_T = 0$
- $V_{CT} > V_{Thn}$, T_n – on, $I_O = I_T > 0$

$$V_{PS} = RI_O + V_O$$

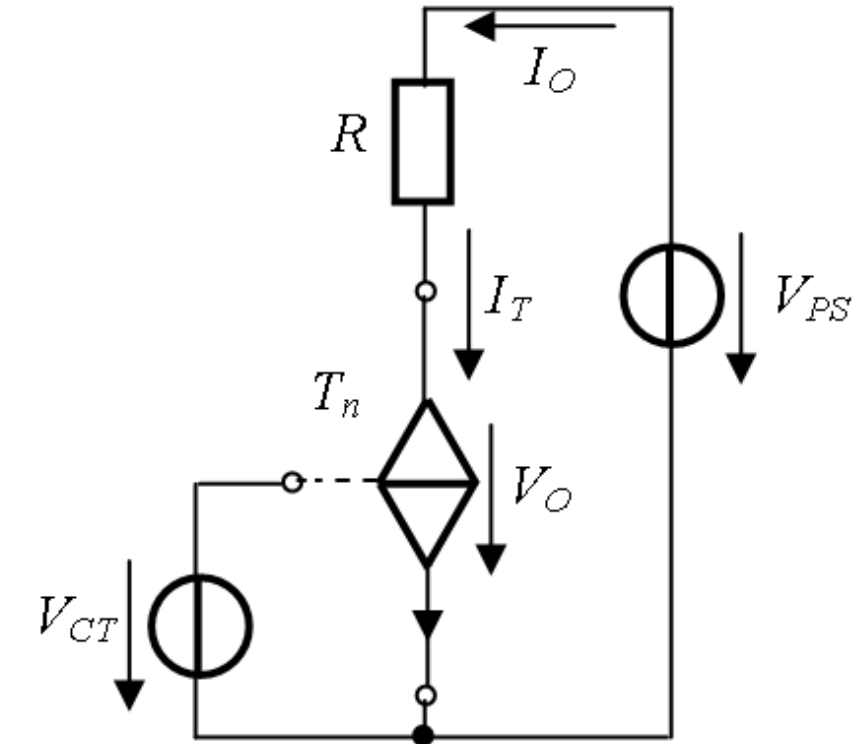
$$V_O = V_{PS} - RI_O$$

$$V_{CT} \uparrow, I_O \uparrow, V_O \downarrow$$

$$V_{O,min} = 0$$

$$I_{Oex} = \frac{V_{PS}}{R}$$

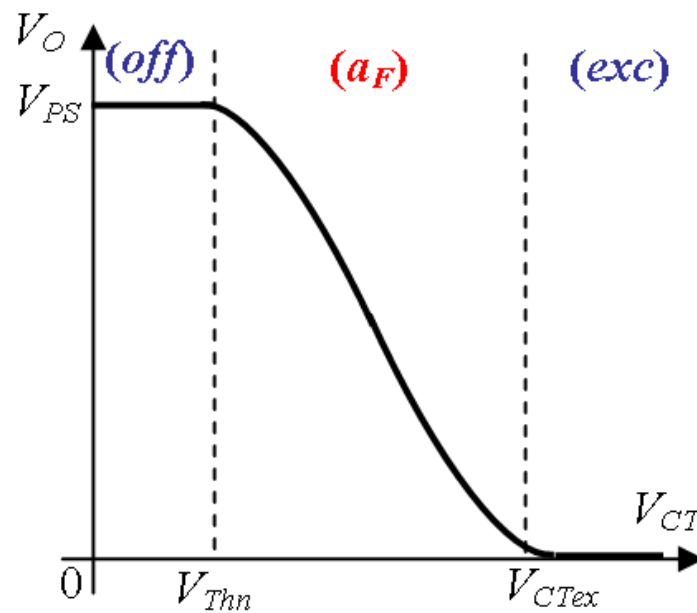
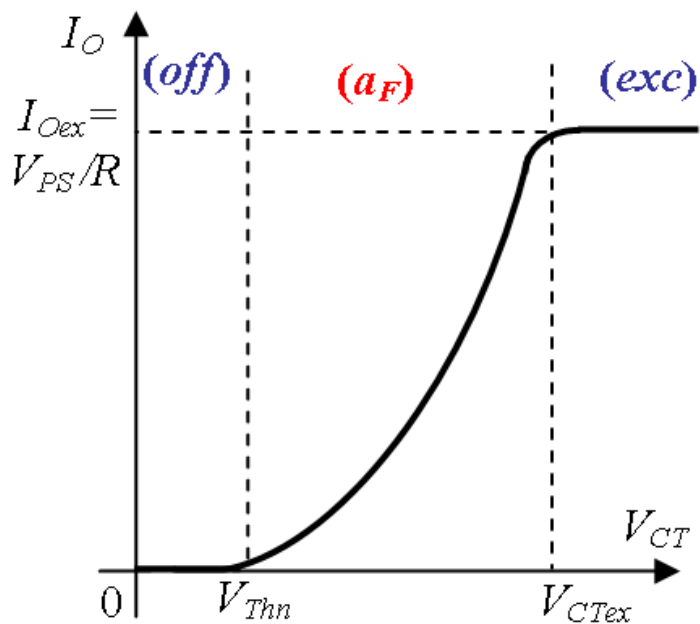
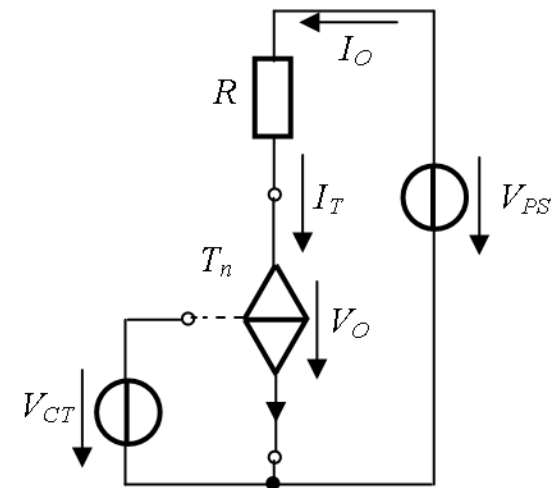
I_{Oex} – maximum possible value of I_O , in the given circuit



Plots for $I_O(V_{CT})$, $V_O(V_{CT})$?

➤ Transfer characteristics

- $V_{CT} < V_{Thn}$, T_n – off, $I_O = I_T = 0$
- $V_{CT} > V_{Thn}$, T_n – on, $I_O = I_T > 0$



➤ Transfer characteristics

- Two extreme regions, **passive**:

- **cutoff (off)**

$I_O = 0; V_O > 0$; ideal switch in **off** state

- **extreme conduction (exc)**

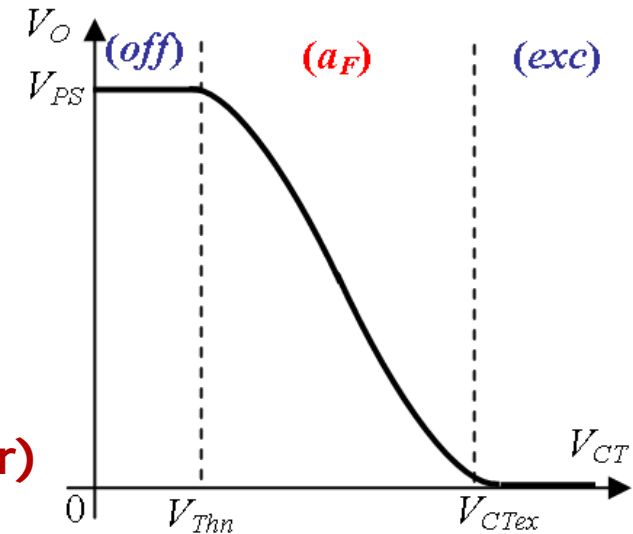
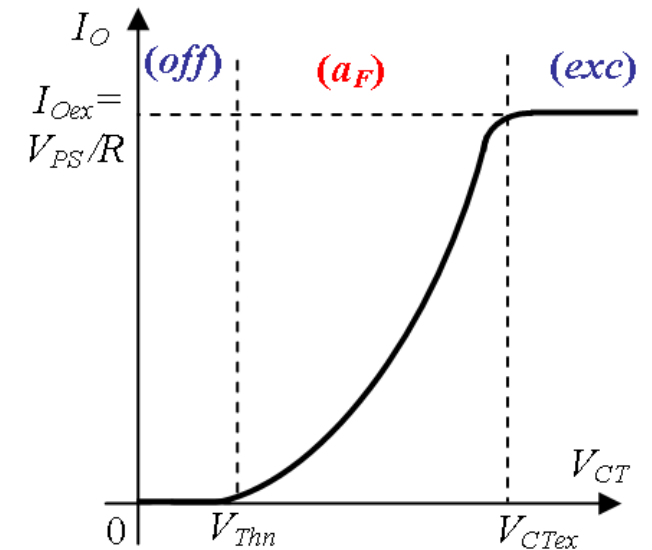
$I_O = I_{Oex}; V_O = 0$; ideal switch in **on** state

$V_{CT} < V_{Thn}$ or $V_{CT} > V_{CTex}$ - **switching transistor**

- An intermediate region, **active**:

active forward region (**a_F**)

$V_{Thn} < V_{CT} < V_{CTex}$ - **permanent conduction (amplifier)**



➤ p-type transistors

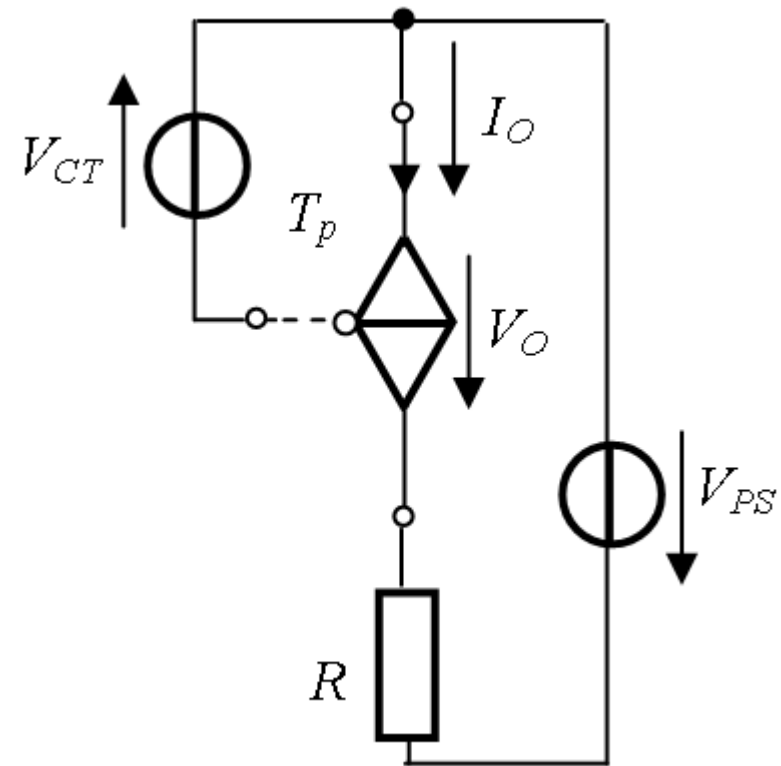
Using the p-type transistor, T_p , in a circuit

- series supply – voltage source
- parallel supply – current source

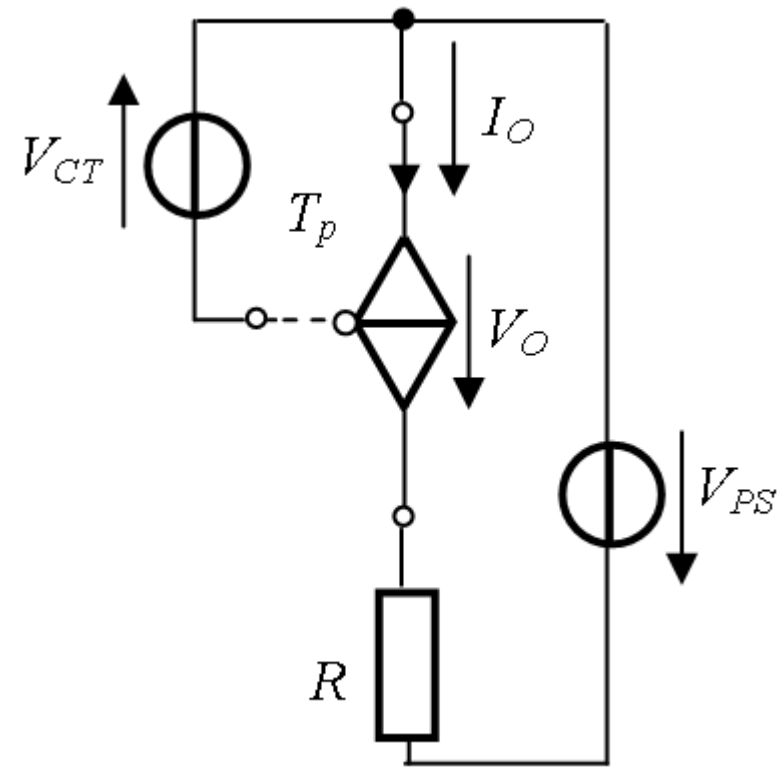
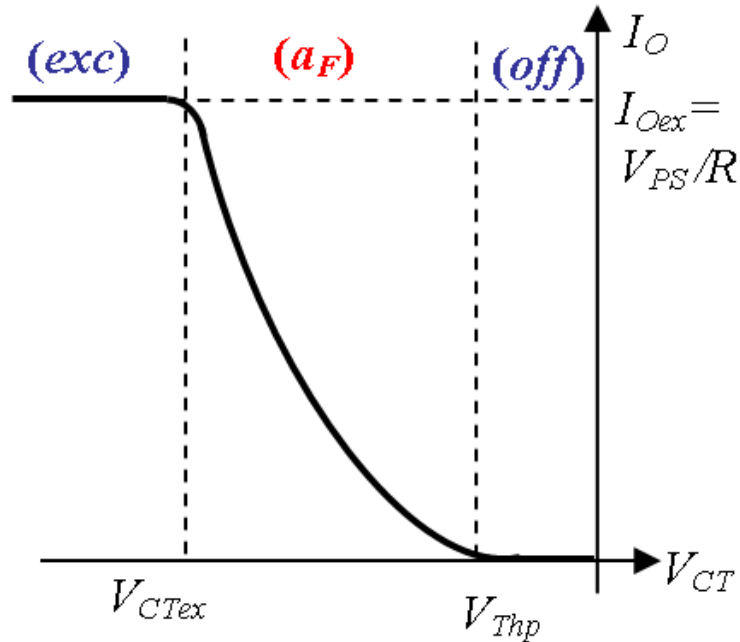
Output quantities: I_O , V_O

Transfer characteristics: $I_O(V_{CT})$, $V_O(V_{CT})$

$$I_T = I_O$$

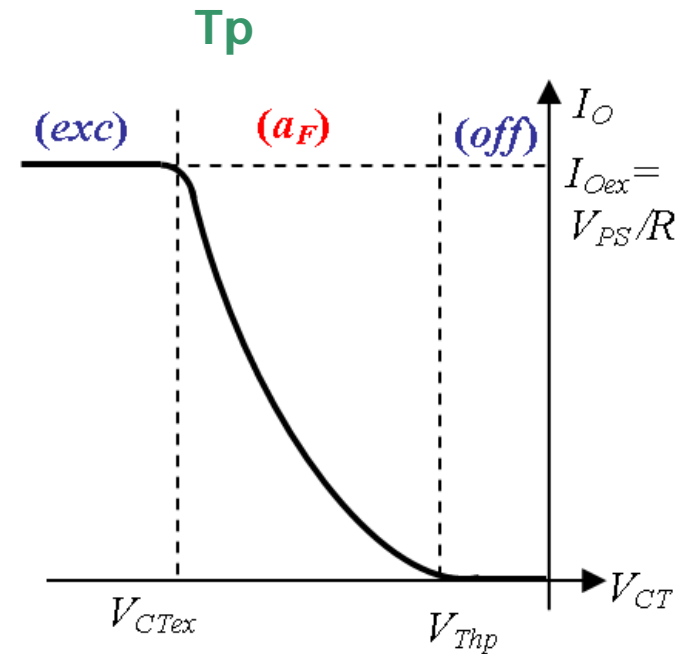
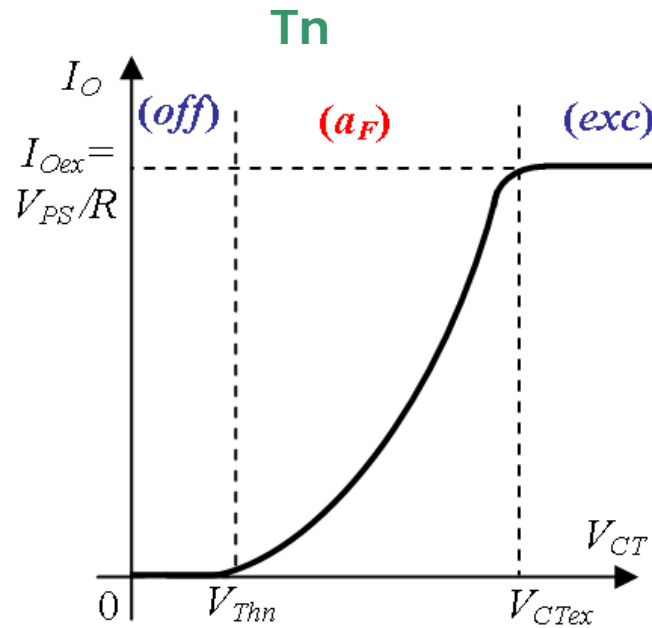


➤ Transfer characteristics



- cutoff (off) $V_{CT} > V_{Thp}$
- extreme conduction (exc) $V_{CT} < V_{CTex}$
- active region (a_F) $V_{CTex} < V_{CT} < V_{Thp}$

➤ Who determines the boundaries between operating regions?



- border (off) - (a_F), $V_{CT} = V_{Th}$: the **transistor** (by its V_{Th})
- border (a_F) - (exc), $V_{CT} = V_{CTex}$:
transistor (by means of $I_O(V_{CT})$)
R and **V_{PS}** (by I_{Oex})

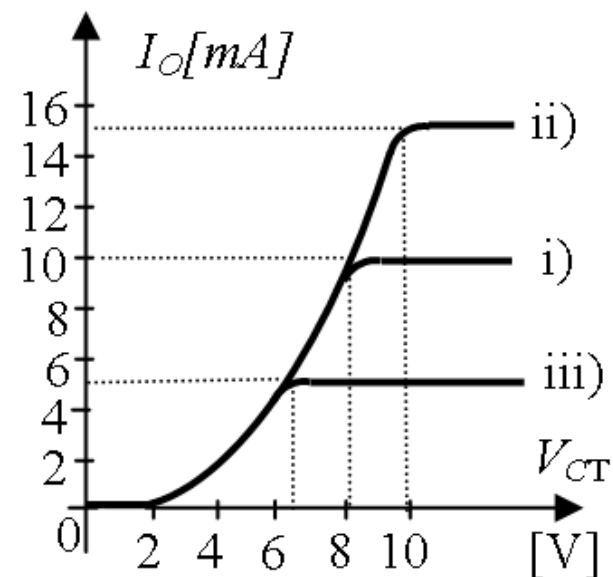
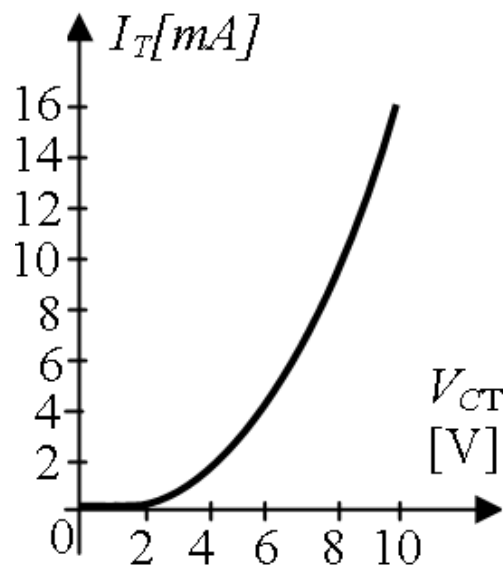
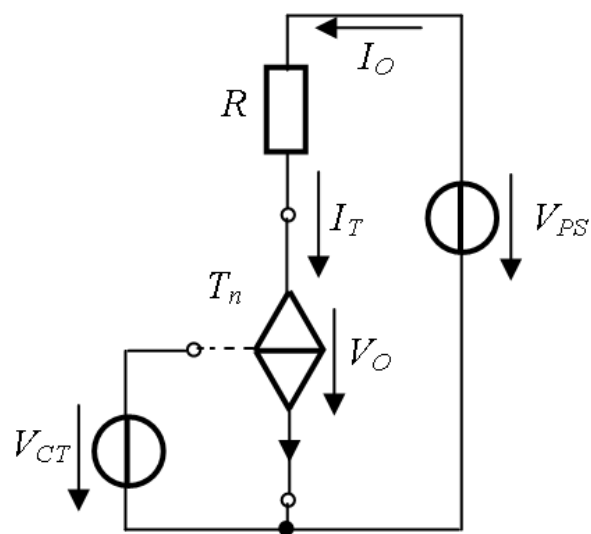
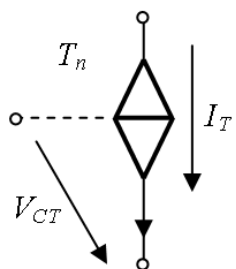
Example

- Determine the operating region of T for:

i) $V_{PS} = 10V$; $R = 1\text{ k}\Omega$

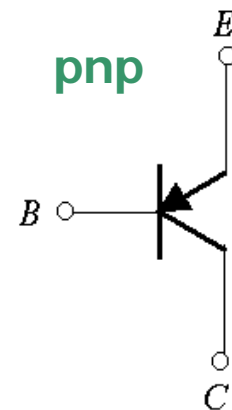
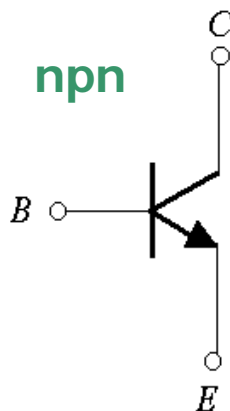
ii) $V_{PS} = 15\text{ V}$; $R = 1\text{ k}\Omega$

iii) $V_{PS} = 10\text{ V}$; $R = 2\text{ k}\Omega$



➤ Bipolar junction transistors (BJTs)

Circuit symbols



B – base

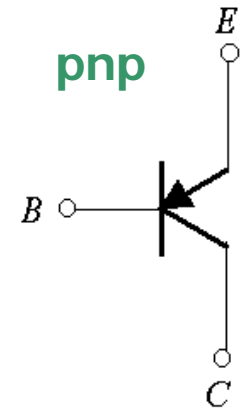
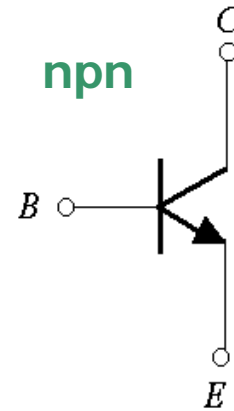
C – collector

E – emitter

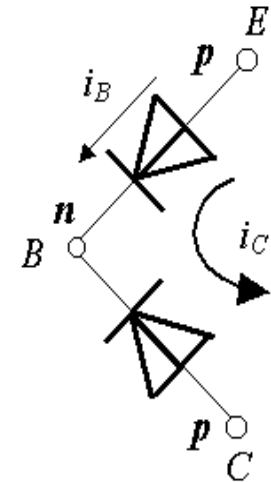
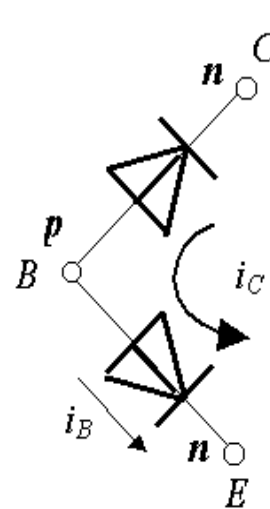
The arrow on the emitter terminal indicates the direction of the positive current.

➤ Bipolar junction transistors (BJTs)

An ohmmeter's view



!There are interactions between the two junctions!



Summary

Looks like transistors are not that scary, after all! Their fundamental features were revealed today:

- Types of transistors
- Operating principle. Operating regions.
- n-type transistors. Transfer characteristics.
- p-type transistors. Transfer characteristics.
- Bipolar junction transistors (BJTs)

Next week: BJT operation

To do: Ask your grandparents what household item they used to call “Transistor”